

CoolSiC™ Hybrid Discrete - TRENCHSTOP™ 5 H5 IGBT co-packed with half-rated 6th generation CoolSiC™ diode

Features

- $V_{CE} = 650\text{ V}$
- $I_C = 50\text{ A}$
- Ultra-low switching losses due to the combination of TRENCHSTOP™ 5 and CoolSiC™ technology
- Benchmark efficiency in hard switching topologies
- Plug-and-play replacement of pure silicon devices
- Maximum junction temperature $T_{vjmax} = 175^\circ\text{C}$
- Qualified according to JEDEC for target applications
- Pb-free lead plating; RoHS compliant
- Complete product spectrum and PSpice Models: <http://www.infineon.com/igbt/>

Potential applications

- Industrial SMPS
- Industrial UPS
- Solar string inverter
- Energy storage
- Charger

Product validation

- Qualified for applications listed above based on the test conditions in the relevant tests of JEDEC20/22

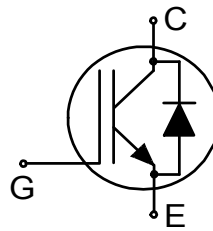
Description

Package pin definition:

- Pin G - gate
- Pin C & backside - collector
- Pin E - emitter



- Lead-free
- Green
- Halogen-free
- RoHS



Type	Package	Marking
IKW50N65RH5	PG-TO247-3	K50ERH5

Table of contents

	Description	1
	Features	1
	Potential applications	1
	Product validation	1
	Table of contents	2
1	Package	3
2	IGBT	3
3	Diode	6
4	Characteristics diagrams	7
5	Package outlines	13
6	Testing conditions	14
	Revision history	15
	Disclaimer	16

1 Package

Table 1 Characteristic values

Parameter	Symbol	Note or test condition	Values			Unit
			Min.	Typ.	Max.	
Internal emitter inductance measured 5 mm (0.197 in.) from case	L_E			13		nH
Storage temperature	T_{stg}		-55		150	°C
Soldering temperature		wave soldering 1.6 mm (0.063 in.) from case for 10 s			260	°C
Mounting torque	M	M3 screw Maximum of mounting process: 3			0.6	Nm
Thermal resistance, junction-ambient	$R_{th(j-a)}$				40	K/W

2 IGBT

Table 2 Maximum rated values

Parameter	Symbol	Note or test condition	Values	Unit	
Collector-emitter voltage	V_{CE}	$T_{vj} \geq 25\text{ °C}$	650	V	
DC collector current, limited by T_{vjmax}	I_C	limited by bondwire	$T_c = 25\text{ °C}$	80	A
			$T_c = 100\text{ °C}$	56	
Pulsed collector current, t_p limited by T_{vjmax}	I_{Cpulse}		200	A	
Turn-off safe operating area		$V_{CE} \leq 650\text{ V}, t_p = 1\text{ }\mu\text{s}, T_{vj} \leq 175\text{ °C}$	200	A	
Gate-emitter voltage	V_{GE}		± 20	V	
Transient gate-emitter voltage	V_{GE}	$t_p \leq 10\text{ }\mu\text{s}, D < 0.01$	± 30	V	
Power dissipation	P_{tot}		$T_c = 25\text{ °C}$	305	W
			$T_c = 100\text{ °C}$	152.5	

Table 3 Characteristic values

Parameter	Symbol	Note or test condition	Values			Unit	
			Min.	Typ.	Max.		
Collector-emitter saturation voltage	V_{CEsat}	$I_C = 50\text{ A}, V_{GE} = 15\text{ V}$	$T_{vj} = 25\text{ °C}$		1.65	2.1	V
			$T_{vj} = 125\text{ °C}$		1.85		
			$T_{vj} = 175\text{ °C}$		1.95		
Gate-emitter threshold voltage	V_{GEth}	$I_C = 0.5\text{ mA}, V_{CE} = V_{GE}$	3.2	4	4.8	V	

(table continues...)

Table 3 (continued) Characteristic values

Parameter	Symbol	Note or test condition	Values			Unit	
			Min.	Typ.	Max.		
Zero gate-voltage collector current	I_{CES}	$V_{CE} = 650 \text{ V}, V_{GE} = 0 \text{ V}$	$T_{vj} = 25 \text{ }^\circ\text{C}$			700	μA
			$T_{vj} = 175 \text{ }^\circ\text{C}$		2000		
Zero gate-voltage collector current	I_{CES}	$V_{CE} = 480 \text{ V}, V_{GE} = 0 \text{ V}$	$T_{vj} = 25 \text{ }^\circ\text{C}$			25	μA
Gate-emitter leakage current	I_{GES}	$V_{CE} = 0 \text{ V}, V_{GE} = 20 \text{ V}$				100	nA
Transconductance	g_{fs}	$I_C = 50 \text{ A}, V_{CE} = 20 \text{ V}$		62			S
Input capacitance	C_{ies}	$V_{CE} = 25 \text{ V}, V_{GE} = 0 \text{ V}, f = 250 \text{ kHz}$		2660			pF
Output capacitance	C_{oes}	$V_{CE} = 25 \text{ V}, V_{GE} = 0 \text{ V}, f = 250 \text{ kHz}$		320			pF
Reverse transfer capacitance	C_{res}	$V_{CE} = 25 \text{ V}, V_{GE} = 0 \text{ V}, f = 250 \text{ kHz}$		10			pF
Gate charge	Q_G	$I_C = 50 \text{ A}, V_{GE} = 15 \text{ V}, V_{CC} = 520 \text{ V}$		120			nC
Turn-on delay time	$t_{d(on)}$	$V_{CC} = 400 \text{ V}, V_{GE} = 0/15 \text{ V}, R_{Gon} = 12 \text{ } \Omega, R_{Goff} = 12 \text{ } \Omega, L_\sigma = 30 \text{ nH}, C_\sigma = 30 \text{ pF}$	$T_{vj} = 25 \text{ }^\circ\text{C}, I_C = 25 \text{ A}$		22		ns
			$T_{vj} = 25 \text{ }^\circ\text{C}, I_C = 5 \text{ A}$		20		
			$T_{vj} = 150 \text{ }^\circ\text{C}, I_C = 25 \text{ A}$		20		
			$T_{vj} = 150 \text{ }^\circ\text{C}, I_C = 5 \text{ A}$		18		
Rise time (inductive load)	t_r	$V_{CC} = 400 \text{ V}, V_{GE} = 0/15 \text{ V}, R_{Gon} = 12 \text{ } \Omega, R_{Goff} = 12 \text{ } \Omega, L_\sigma = 30 \text{ nH}, C_\sigma = 30 \text{ pF}$	$T_{vj} = 25 \text{ }^\circ\text{C}, I_C = 25 \text{ A}$		7		ns
			$T_{vj} = 25 \text{ }^\circ\text{C}, I_C = 5 \text{ A}$		3		
			$T_{vj} = 150 \text{ }^\circ\text{C}, I_C = 25 \text{ A}$		9		
			$T_{vj} = 150 \text{ }^\circ\text{C}, I_C = 5 \text{ A}$		4		
Turn-off delay time	$t_{d(off)}$	$V_{CC} = 400 \text{ V}, V_{GE} = 0/15 \text{ V}, R_{Gon} = 12 \text{ } \Omega, R_{Goff} = 12 \text{ } \Omega, L_\sigma = 30 \text{ nH}, C_\sigma = 30 \text{ pF}$	$T_{vj} = 25 \text{ }^\circ\text{C}, I_C = 25 \text{ A}$		180		ns
			$T_{vj} = 25 \text{ }^\circ\text{C}, I_C = 5 \text{ A}$		200		
			$T_{vj} = 150 \text{ }^\circ\text{C}, I_C = 25 \text{ A}$		200		
			$T_{vj} = 150 \text{ }^\circ\text{C}, I_C = 5 \text{ A}$		250		

(table continues...)

Table 3 (continued) Characteristic values

Parameter	Symbol	Note or test condition	Values			Unit	
			Min.	Typ.	Max.		
Fall time (inductive load)	t_f	$V_{CC} = 400\text{ V}, V_{GE} = 0/15\text{ V},$ $R_{Gon} = 12\ \Omega, R_{Goff} = 12\ \Omega,$ $L_\sigma = 30\text{ nH}, C_\sigma = 30\text{ pF}$	$T_{vj} = 25\text{ }^\circ\text{C},$ $I_C = 25\text{ A}$		18		ns
			$T_{vj} = 25\text{ }^\circ\text{C}, I_C = 5\text{ A}$		25		
			$T_{vj} = 150\text{ }^\circ\text{C},$ $I_C = 25\text{ A}$		25		
			$T_{vj} = 150\text{ }^\circ\text{C},$ $I_C = 5\text{ A}$		35		
Turn-on energy	E_{on}	$V_{CC} = 400\text{ V}, V_{GE} = 0/15\text{ V},$ $R_{Gon} = 12\ \Omega, R_{Goff} = 12\ \Omega,$ $L_\sigma = 30\text{ nH}, C_\sigma = 30\text{ pF}$	$T_{vj} = 25\text{ }^\circ\text{C},$ $I_C = 25\text{ A}$		0.23		mJ
			$T_{vj} = 25\text{ }^\circ\text{C}, I_C = 5\text{ A}$		0.05		
			$T_{vj} = 150\text{ }^\circ\text{C},$ $I_C = 25\text{ A}$		0.3		
			$T_{vj} = 150\text{ }^\circ\text{C},$ $I_C = 5\text{ A}$		0.08		
Turn-off energy	E_{off}	$V_{CC} = 400\text{ V}, V_{GE} = 0/15\text{ V},$ $R_{Gon} = 12\ \Omega, R_{Goff} = 12\ \Omega,$ $L_\sigma = 30\text{ nH}, C_\sigma = 30\text{ pF}$	$T_{vj} = 25\text{ }^\circ\text{C},$ $I_C = 25\text{ A}$		0.18		mJ
			$T_{vj} = 25\text{ }^\circ\text{C}, I_C = 5\text{ A}$		0.05		
			$T_{vj} = 150\text{ }^\circ\text{C},$ $I_C = 25\text{ A}$		0.27		
			$T_{vj} = 150\text{ }^\circ\text{C},$ $I_C = 5\text{ A}$		0.08		
Total switching energy	E_{ts}	$V_{CC} = 400\text{ V}, V_{GE} = 0/15\text{ V},$ $R_{Gon} = 12\ \Omega, R_{Goff} = 12\ \Omega,$ $L_\sigma = 30\text{ nH}, C_\sigma = 30\text{ pF}$	$T_{vj} = 25\text{ }^\circ\text{C},$ $I_C = 25\text{ A}$		0.41		mJ
			$T_{vj} = 25\text{ }^\circ\text{C}, I_C = 5\text{ A}$		0.1		
			$T_{vj} = 150\text{ }^\circ\text{C},$ $I_C = 25\text{ A}$		0.57		
			$T_{vj} = 150\text{ }^\circ\text{C},$ $I_C = 5\text{ A}$		0.16		
IGBT thermal resistance, junction-case	$R_{th(j-c)}$				0.5	K/W	
Operating junction temperature	T_{vj}		-40		175	$^\circ\text{C}$	

3 Diode

Table 4 Maximum rated values

Parameter	Symbol	Note or test condition	Values	Unit	
Repetitive peak reverse voltage	V_{RRM}	$T_{vj} \geq 25\text{ °C}$	650	V	
Diode forward current, limited by T_{vjmax}	I_F		$T_c = 25\text{ °C}$	33.7	A
			$T_c = 100\text{ °C}$	22.8	
Diode pulsed current, t_p limited by T_{vjmax} ¹⁾	I_{Fpulse}		75	A	

1) Pulse current level depends on T_{vj} of diode chip, see also Fig. "Maximum pulse current as a function of junction temperature"

Table 5 Characteristic values

Parameter	Symbol	Note or test condition	Values			Unit
			Min.	Typ.	Max.	
Diode forward voltage	V_F	$I_F = 20\text{ A}$	$T_{vj} = 25\text{ °C}$	1.35	1.5	V
			$T_{vj} = 125\text{ °C}$	1.55		
			$T_{vj} = 175\text{ °C}$	1.65		
Diode thermal resistance, junction-case	$R_{th(j-c)}$				1.5	K/W
Operating junction temperature	T_{vj}		-40		175	°C

Note: For optimum lifetime and reliability, Infineon recommends operating conditions that do not exceed 80% of the maximum ratings stated in this datasheet.

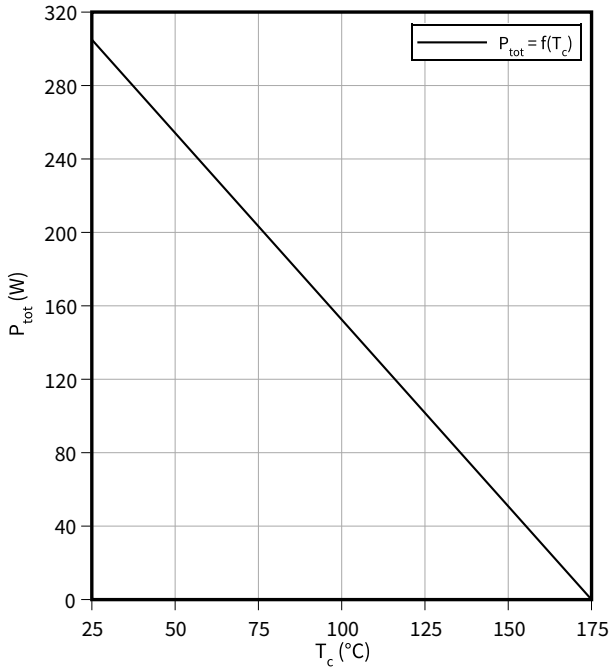
Electrical Characteristic at $T_{vj} = 25\text{ °C}$, unless otherwise specified.

Dynamic test circuit, parasitic inductance L_σ , parasitic capacitor C_σ from Fig. E. Energy losses include "tail" and diode reverse recovery.

4 Characteristics diagrams

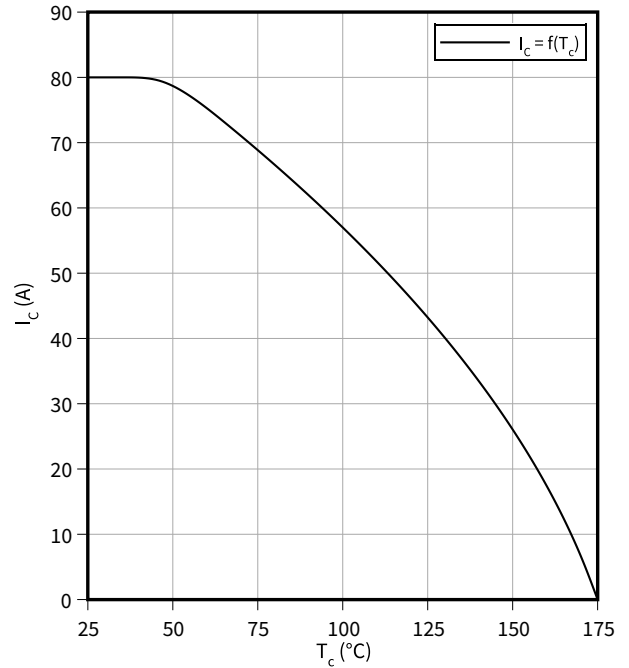
Power dissipation as a function of case temperature

$P_{tot} = f(T_c)$
 $T_{vj} \leq 175\text{ °C}$



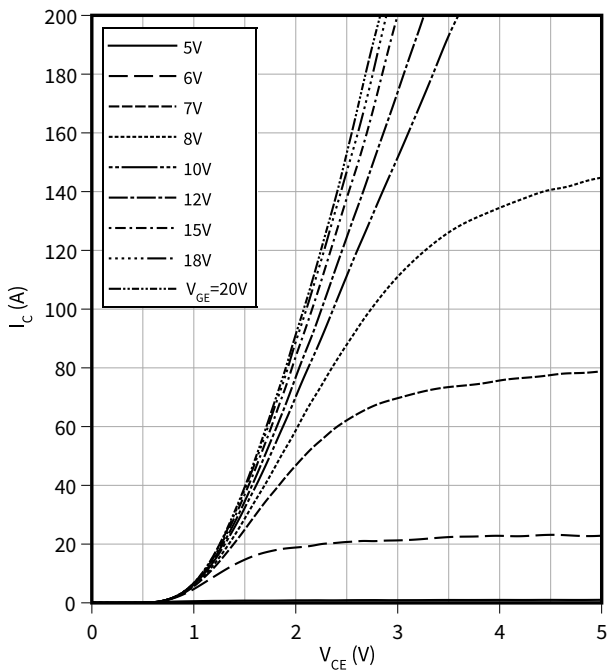
Collector current as a function of case temperature

$I_C = f(T_c)$
 $T_{vj} \leq 175\text{ °C}, V_{GE} \geq 15\text{ V}$



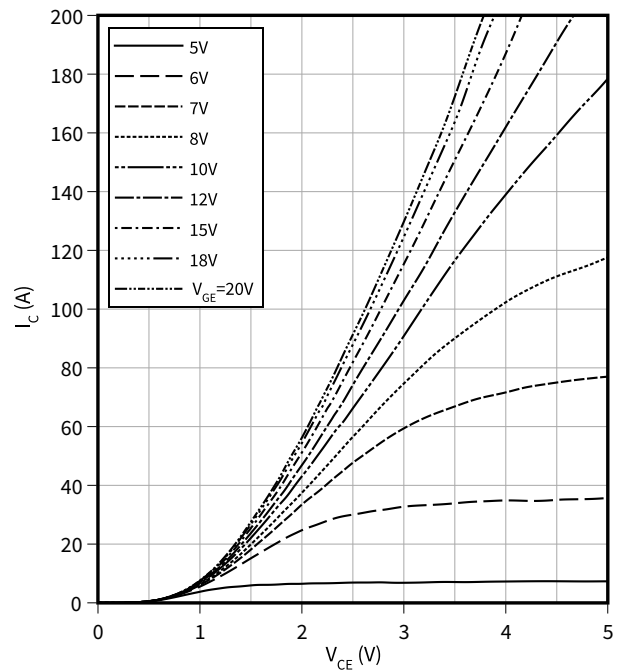
Typical output characteristic

$I_C = f(V_{CE})$
 $T_{vj} = 25\text{ °C}$



Typical output characteristic

$I_C = f(V_{CE})$
 $T_{vj} = 150\text{ °C}$

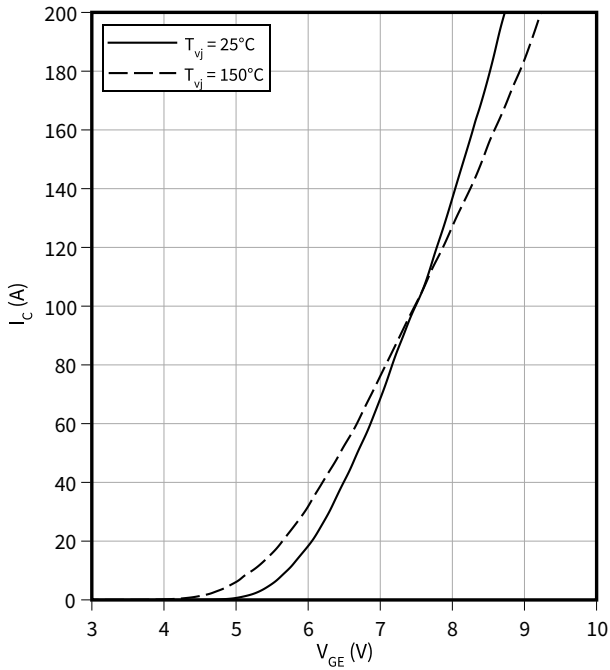


4 Characteristics diagrams

Typical transfer characteristic

$I_C = f(V_{GE})$

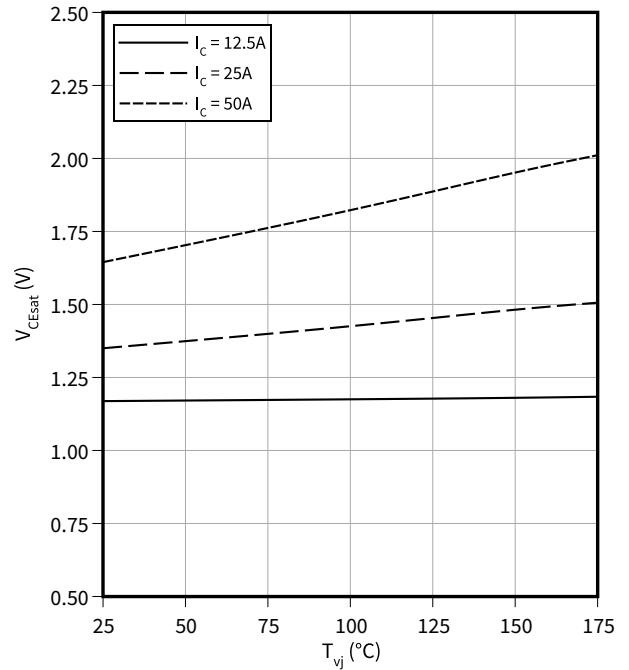
$V_{CE} = 20\text{ V}$



Typical collector-emitter saturation voltage as a function of junction temperature

$V_{CEsat} = f(T_{vj})$

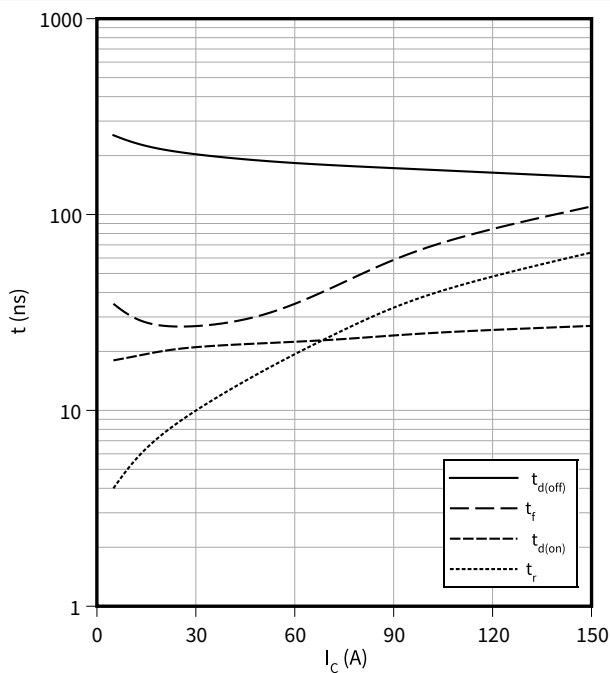
$V_{GE} = 15\text{ V}$



Typical switching times as a function of collector current

$t = f(I_C)$

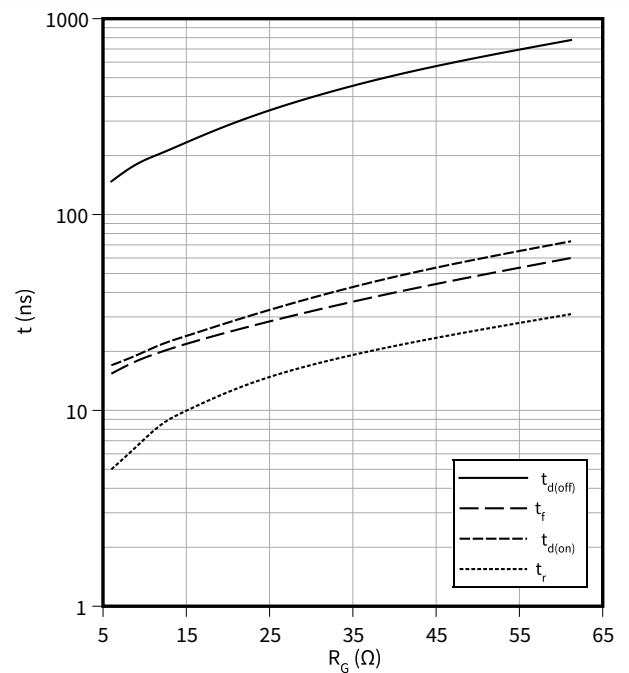
$V_{CC} = 400\text{ V}, T_{vj} = 150^\circ\text{C}, V_{GE} = 0/15\text{ V}, R_G = 12\ \Omega$



Typical switching times as a function of gate resistor

$t = f(R_G)$

$I_C = 25\text{ A}, V_{CC} = 400\text{ V}, T_{vj} = 150^\circ\text{C}, V_{GE} = 0/15\text{ V}$

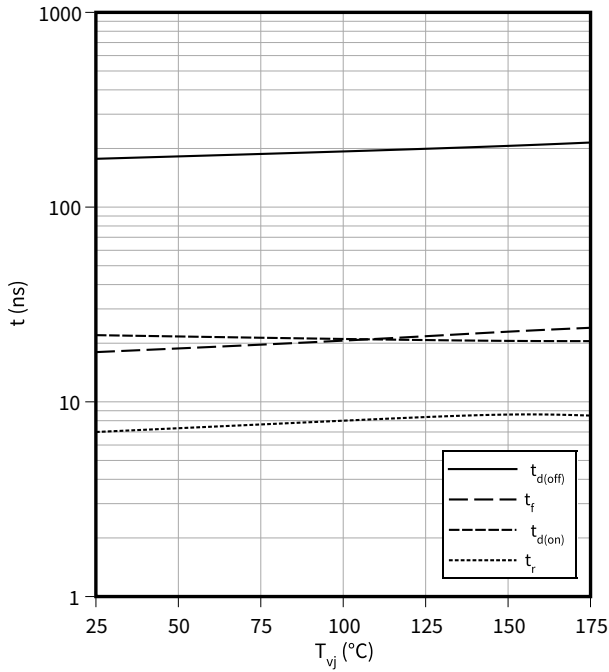


4 Characteristics diagrams

Typical switching times as a function of junction temperature

$t = f(T_{vj})$

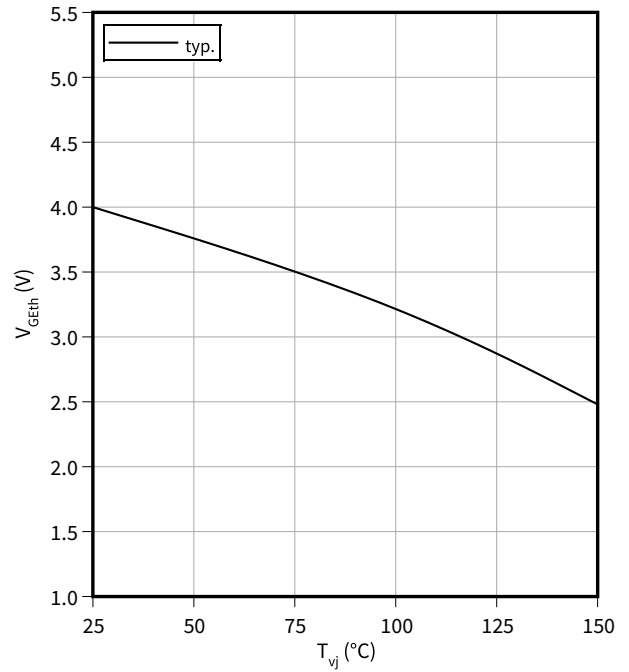
$I_C = 25\text{ A}$, $V_{CC} = 400\text{ V}$, $V_{GE} = 0/15\text{ V}$, $R_G = 12\ \Omega$



Gate-emitter threshold voltage as a function of junction temperature

$V_{GEth} = f(T_{vj})$

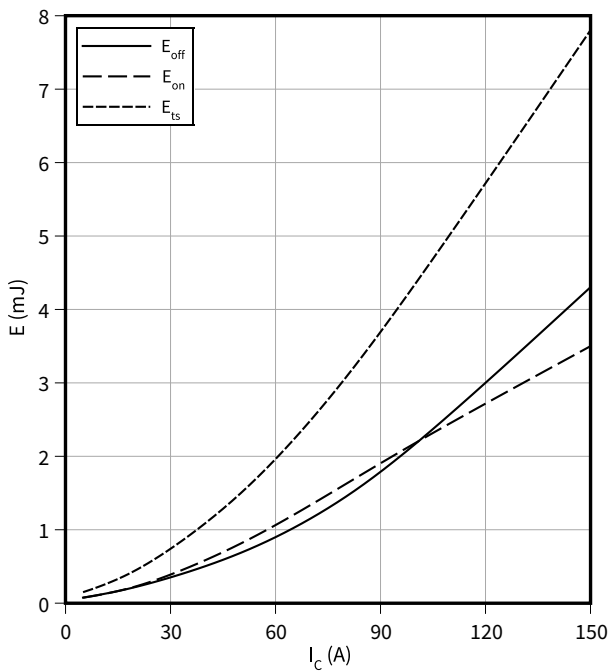
$I_C = 0.5\text{ mA}$



Typical switching energy losses as a function of collector current

$E = f(I_C)$

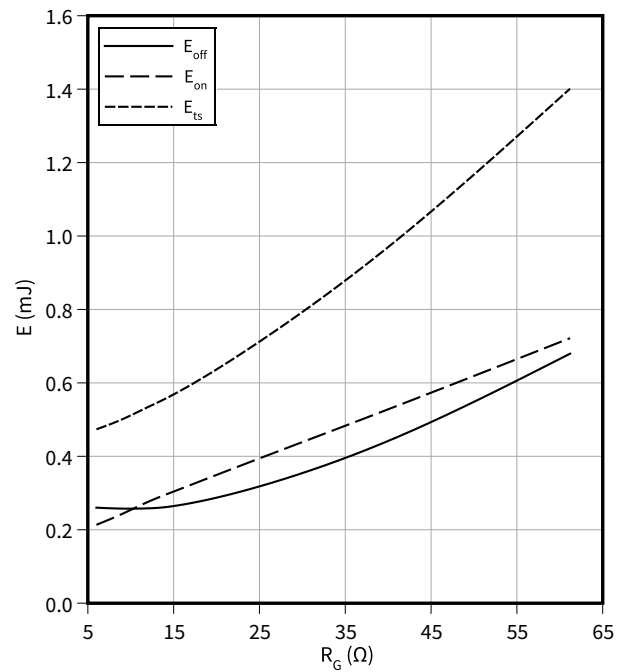
$V_{CC} = 400\text{ V}$, $T_{vj} = 150\text{ °C}$, $V_{GE} = 0/15\text{ V}$, $R_G = 12\ \Omega$



Typical switching energy losses as a function of gate resistor

$E = f(R_G)$

$I_C = 25\text{ A}$, $V_{CC} = 400\text{ V}$, $T_{vj} = 150\text{ °C}$, $V_{GE} = 0/15\text{ V}$

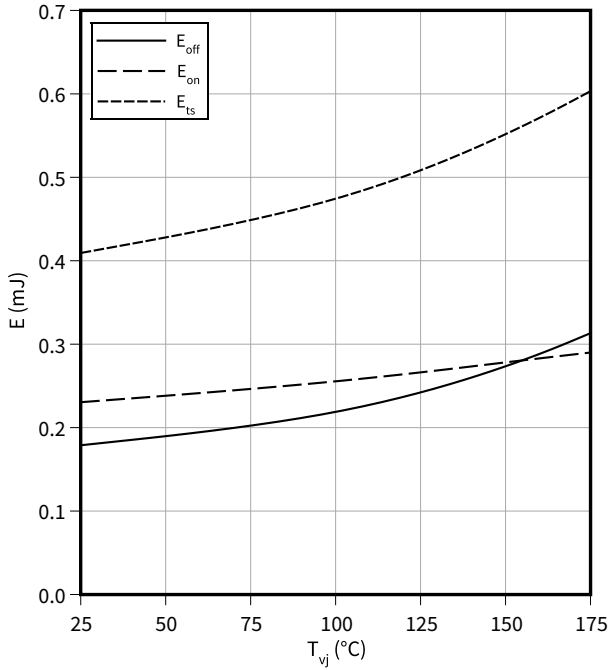


4 Characteristics diagrams

Typical switching energy losses as a function of junction temperature

$E = f(T_{vj})$

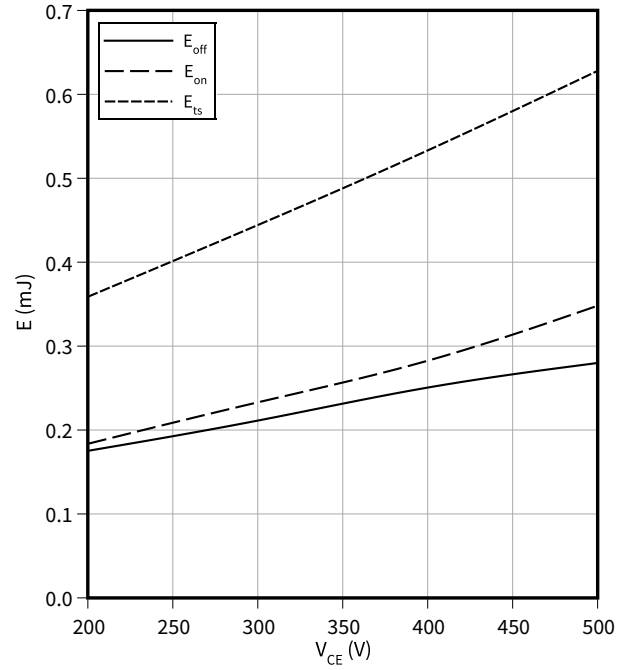
$I_C = 25\text{ A}$, $V_{CC} = 400\text{ V}$, $V_{GE} = 0/15\text{ V}$, $R_G = 12\ \Omega$



Typical switching energy losses as a function of collector emitter voltage

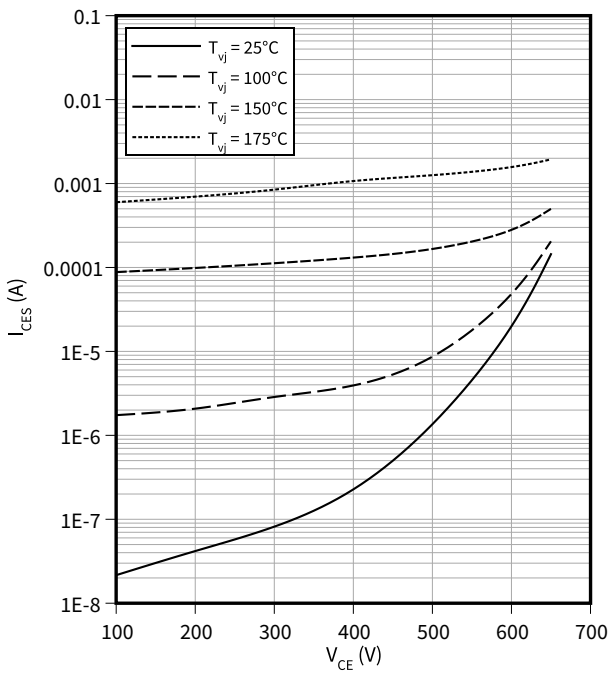
$E = f(V_{CE})$

$I_C = 25\text{ A}$, $T_{vj} = 150\text{ °C}$, $V_{GE} = 0/15\text{ V}$, $R_G = 12\ \Omega$



Typ. reverse current vs. reverse voltage as a function of Tvj

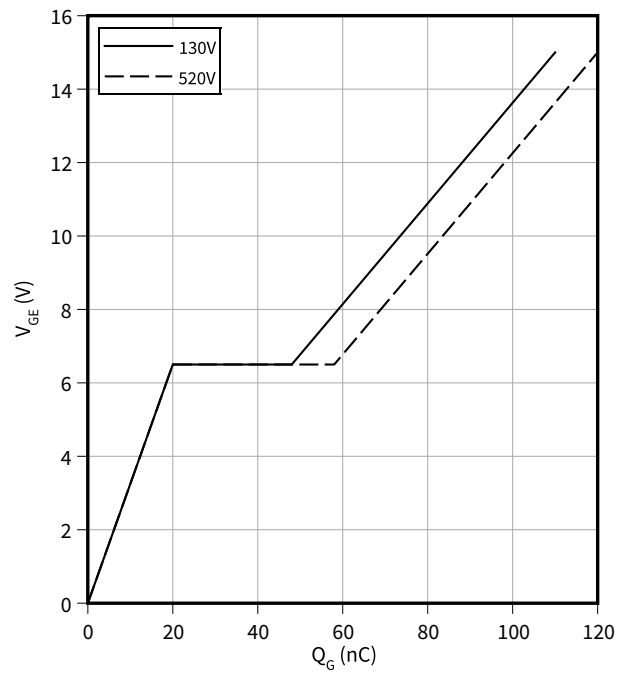
$I_{CES} = f(V_{CE})$



Typical gate charge

$V_{GE} = f(Q_G)$

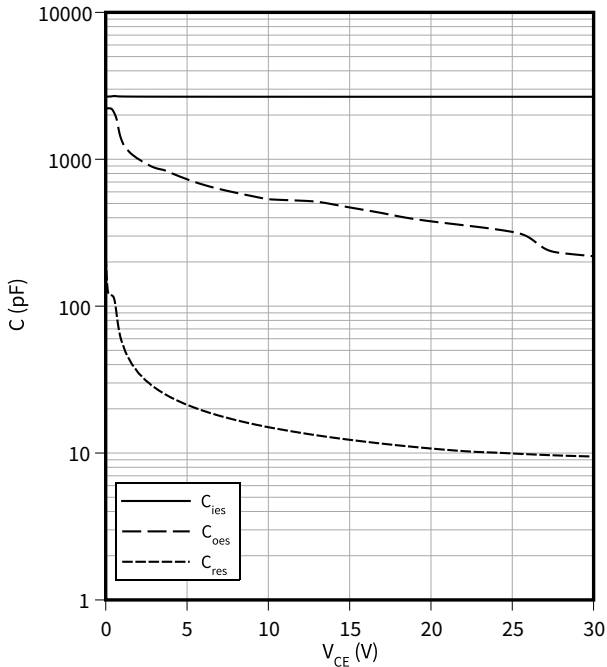
$I_C = 50\text{ A}$



4 Characteristics diagrams

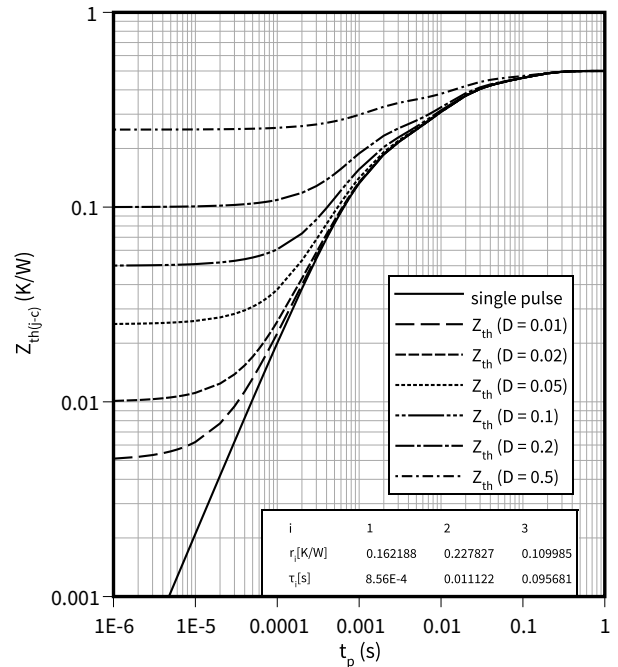
Typical capacitance as a function of collector-emitter voltage

$C = f(V_{CE})$
 $f = 250 \text{ kHz}, V_{GE} = 0 \text{ V}$



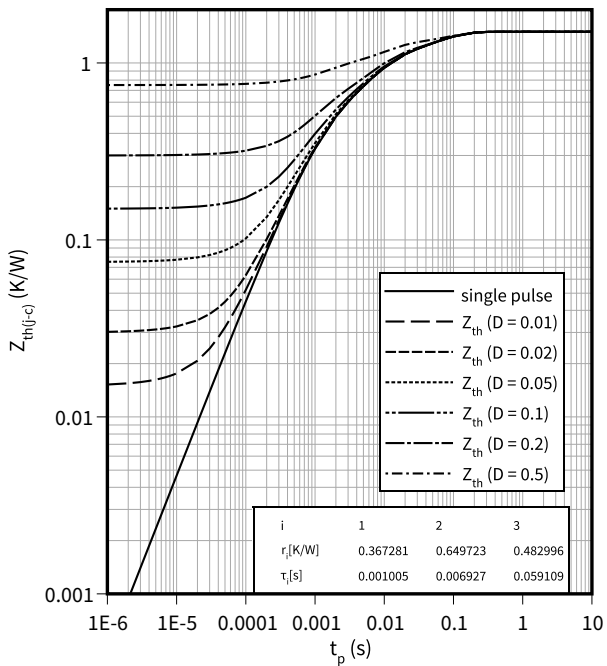
IGBT transient thermal impedance as a function of pulse width

$Z_{th(j-c)} = f(t_p)$
 $D = t_p/T$



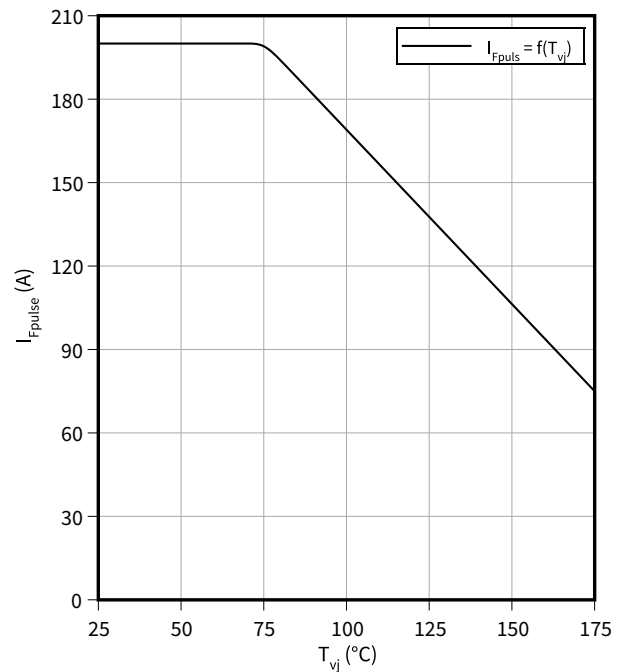
Diode transient thermal impedance as a function of pulse width

$Z_{th(j-c)} = f(t_p)$
 $D = t_p/T$



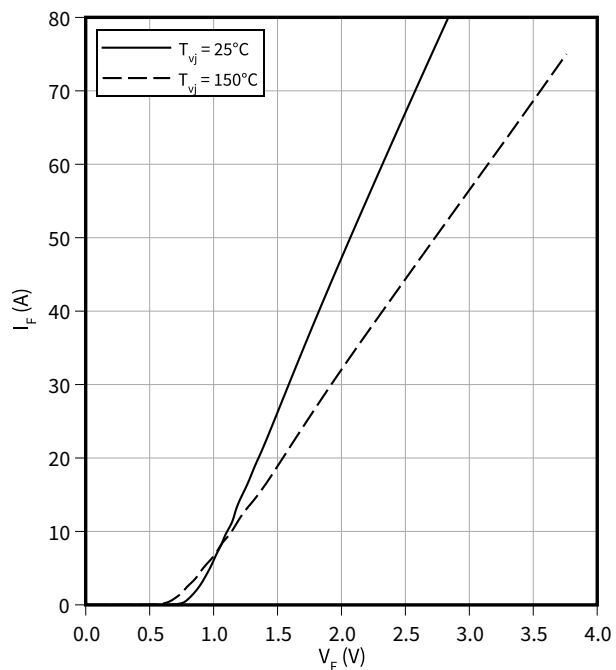
Maximum pulse current as a function of junction temperature

$I_{Fpulse} = f(T_{vj})$



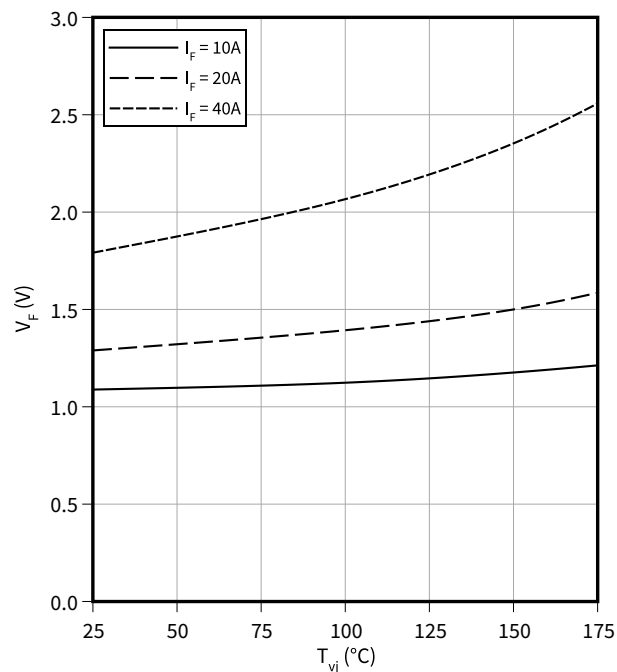
Typical diode forward current as a function of forward voltage

$I_F = f(V_F)$



Typical diode forward voltage as a function of junction temperature

$V_F = f(T_{vj})$



5 Package outlines

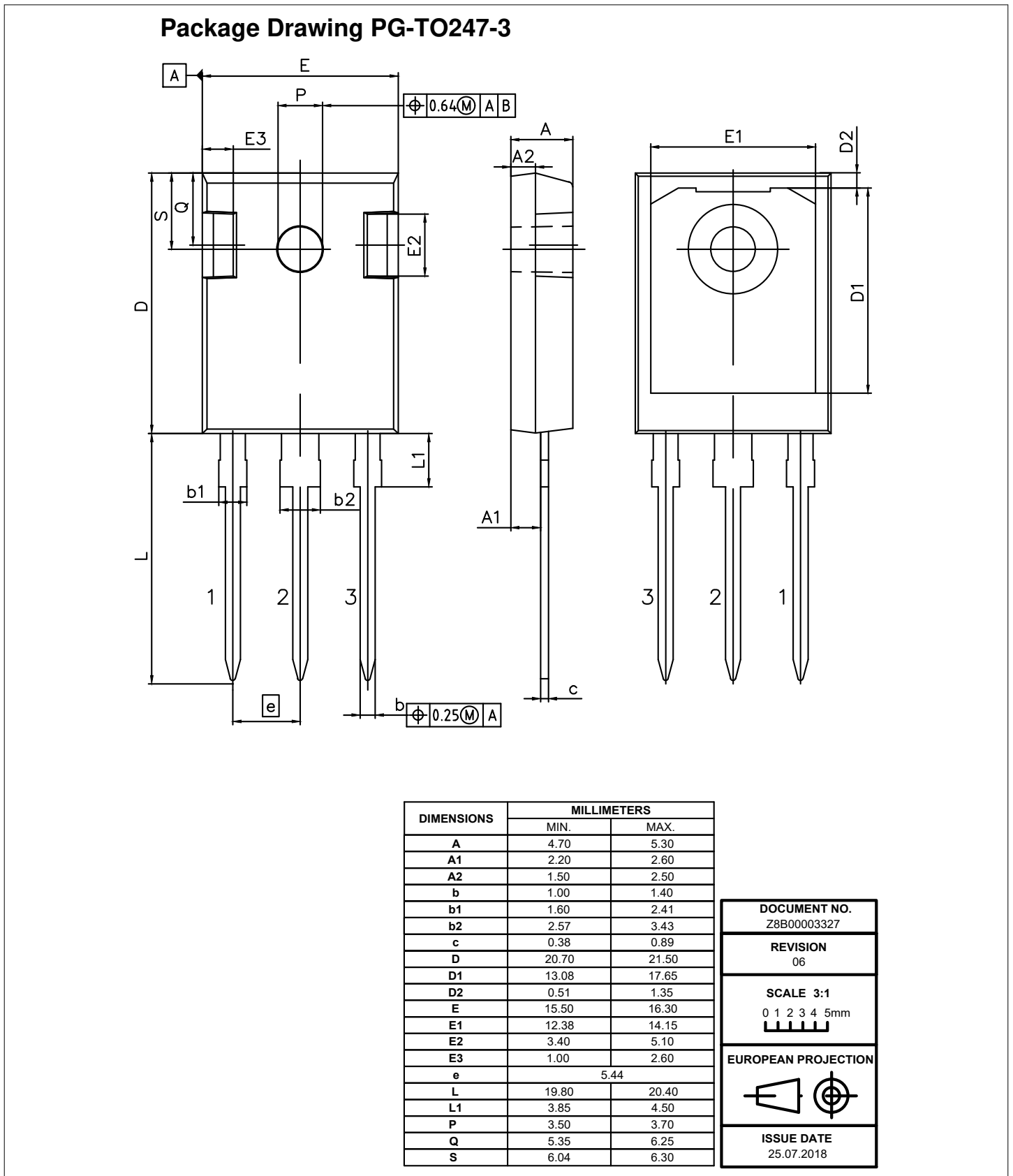


Figure 1

6 Testing conditions

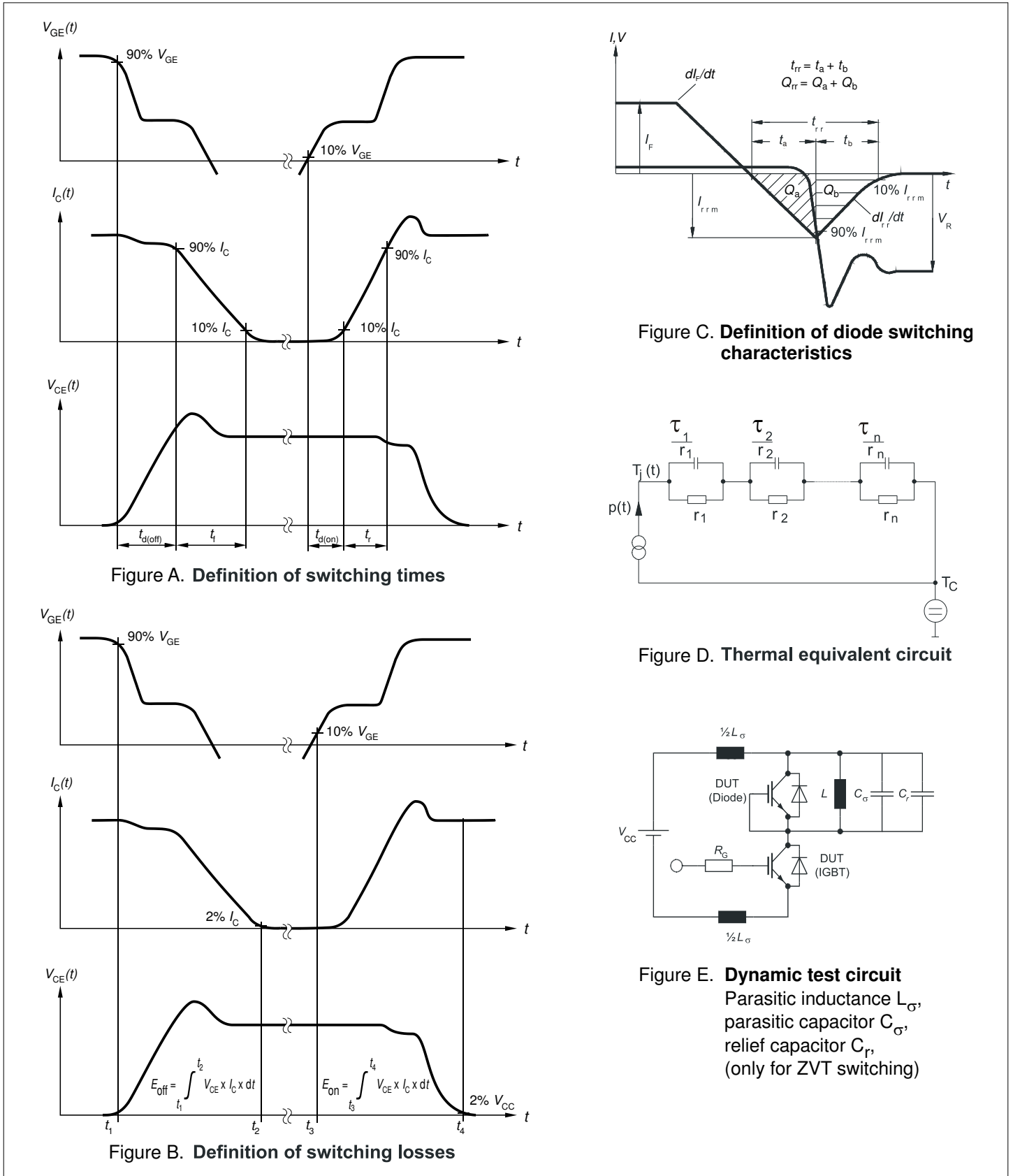


Figure 2

Revision history

Document revision	Date of release	Description of changes
V1.1	2020-03-20	Preliminary Data Sheet
V2.1	2020-07-27	Final Data Sheet
n/a	2020-11-30	Datasheet migrated to a new system with a new layout and new revision number schema: target or preliminary datasheet = 0.xy; final datasheet = 1.xy
1.10	2022-09-22	Rename of product family name from “Hybrid CoolSiC™ IGBT” to “CoolSiC™ hybrid discrete” Corrected the values in table of $Z_{th} = f(t_p)$ diode diagram

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